

12V P-Channel Enhancement Mode MOSFET

Description

The NP1208MR uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.8V. This device is suitable for use as a load switch or in PWM applications.

General Features

- ◆ $V_{DS} = -12V$, $I_D = -8A$
 $R_{DS(ON)}(Typ.) = 14.8m\Omega$ @ $V_{GS} = -4.5V$
 $R_{DS(ON)}(Typ.) = 20.3m\Omega$ @ $V_{GS} = -2.5V$
- ◆ High power and current handling capability
- ◆ Lead free product is acquired
- ◆ Surface mount package

Application

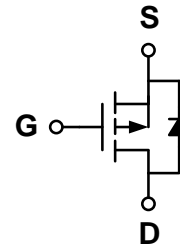
- ◆ PWM applications
- ◆ Load switch

Package

- ◆ SOT-23-3L

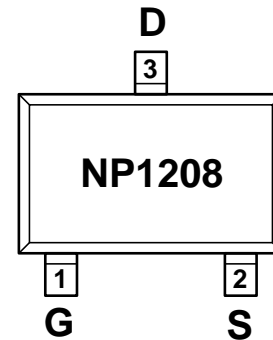


Schematic diagram



Marking and pin assignment

SOT-23-3L
(TOP VIEW)



Ordering Information

Part Number	Storage Temperature	Package	Devices Per Reel
NP1208MR-G	-55°C to +150°C	SOT-23-3L	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

parameter	symbol	limit	unit	
Drain-source voltage	V_{DS}	-12	V	
Gate-source voltage	V_{GS}	±12	V	
Continuous Drain Current	I_D	$T_A = 25^\circ C$	-8	A
		$T_A = 70^\circ C$	-6	A
Pulsed Drain Current ^C	I_{DM}	-24	A	
Maximum power dissipation ^B	P_D	$T_A = 25^\circ C$	1.4	W
		$T_A = 70^\circ C$	0.9	
Operating junction Temperature range	T_j	-55—150	°C	

Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
OFF Characteristics						
Drain-source breakdown voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-12	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=-12V, V_{GS}=0V$	-	-	-1	μA
Gate-body leakage	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$	-	-	± 100	nA
ON Characteristics						
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.4	-0.7	-1	V
Drain-source on-state resistance	$R_{DS(ON)}$	$V_{GS}=-4.5V, I_D=-8A$	-	14.8	18	m Ω
		$V_{GS}=-2.5V, I_D=-8A$	-	20.3	28	
Forward transconductance	gfs	$V_{GS}=-5V, I_D=-8A$	-	5	-	S
Dynamic Characteristics						
Input capacitance	C_{ISS}	$V_{DS}=-6V, V_{GS}=0V$ $f=1.0MHz$	-	1411	-	pF
Output capacitance	C_{OSS}		-	189	-	
Reverse transfer capacitance	C_{RSS}		-	159	-	
Switching Characteristics						
Turn-on delay time	$t_{D(ON)}$	$V_{DS}=-6V$ $I_D=-8A$ $V_{GEN}=-4.5V$ $R_L=1.2ohm$ $R_{GEN}=1ohm$	-	12.5	-	ns
Rise time	t_r		-	35	-	
Turn-off delay time	$t_{D(OFF)}$		-	30	-	
Fall time	t_f		-	10	-	
Total gate charge	Qg	$V_{DS}=-6V, I_D=-8A$ $V_{GS}=-4.5V$	-	29.8	-	nC
Gate-source charge	Qgs		-	1.9	-	
Gate-drain charge	Qgd		-	4.4	-	
DRAIN-SOURCE DIODE CHARACTERISTICS						
Diode forward voltage	V_{SD}	$V_{GS}=0V, I_S=-1.25A$	-	-0.81	-1.2	V

Thermal Characteristics

Parameter	Symbol	Typ.	Max.	Unit
Maximum Junction-to-Ambient ^A	$t \leq 10s$	70	90	$^{\circ}C/W$
Maximum Junction-to-Ambient ^{A D}	Steady-State	100	125	
Maximum Junction-to-Lead	Steady-State	62	80	

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}C$. The value in any given application depends on the user's specific board design.

B. The power dissipation PD is based on $T_{J(MAX)}=150^{\circ}C$, using $\leq 10s$ junction-to-ambient thermal resistance.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^{\circ}C$. Ratings are based on low frequency and duty

Typical Performance Characteristics

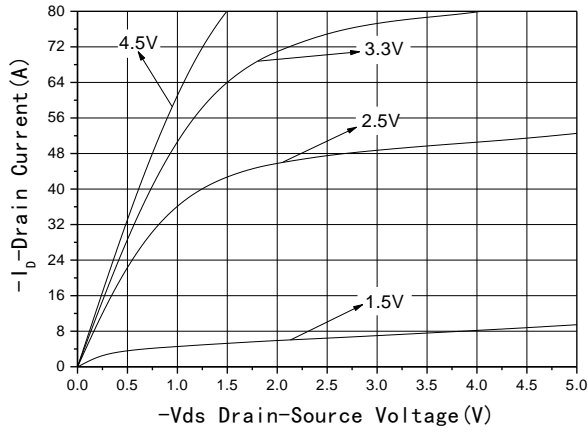


Fig1 Output Characteristics

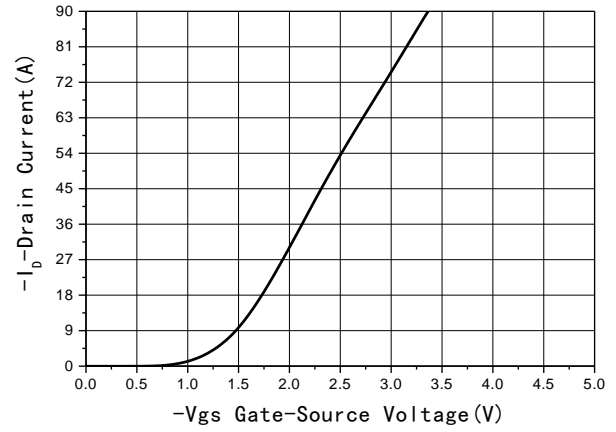


Fig2 Transfer Characteristics

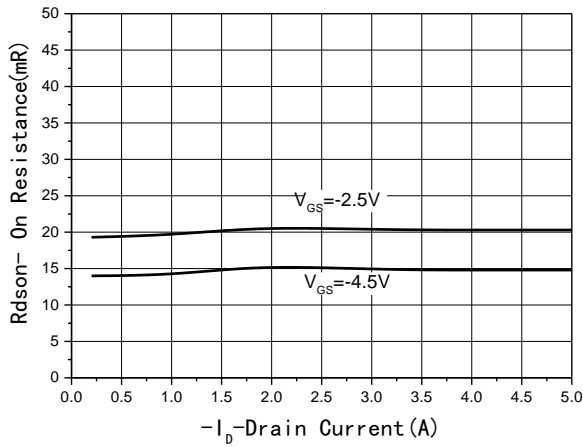


Fig3 $R_{DS(on)}$ -Drain current

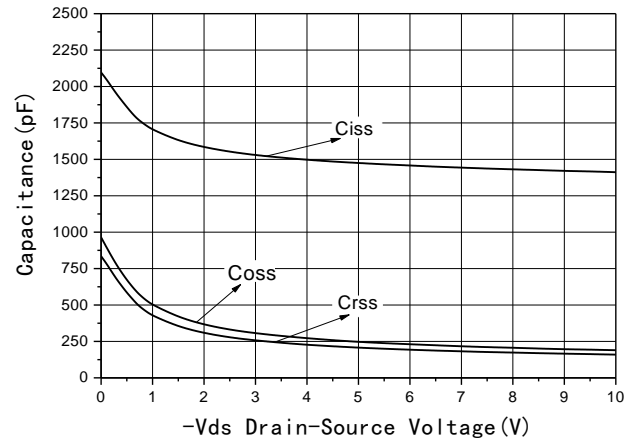


Fig4 Capacitance vs V_{DS}

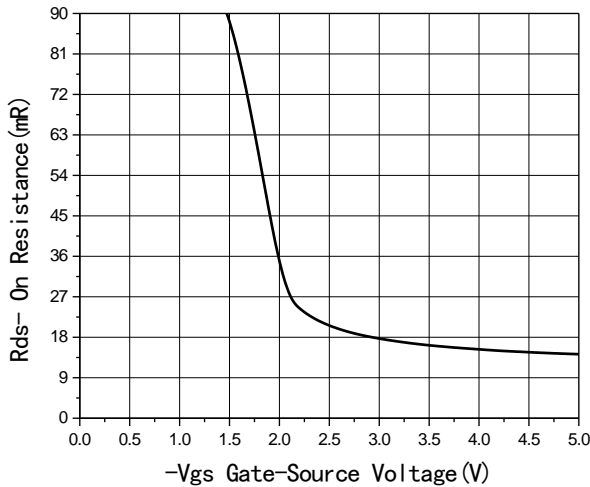


Fig5 $R_{DS(on)}$ -Gate Drain voltage

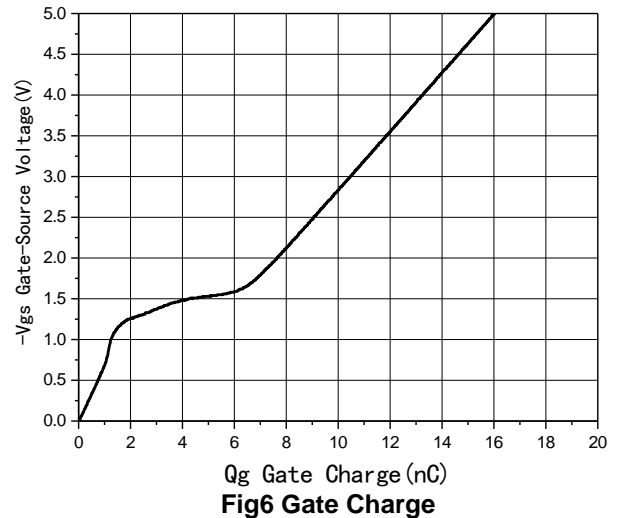


Fig6 Gate Charge

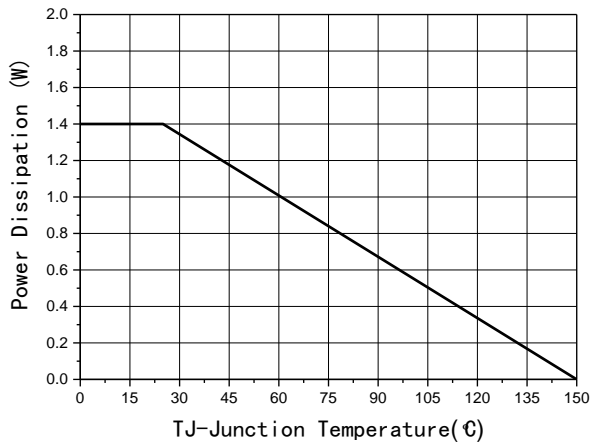


Fig7 Power De-rating

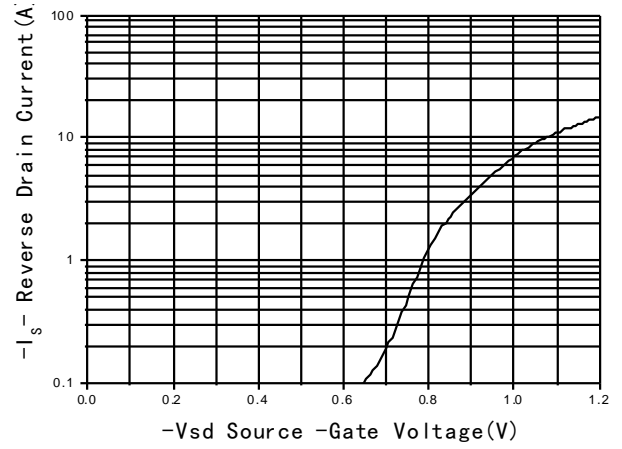


Fig8 Source-Drain Diode Forward

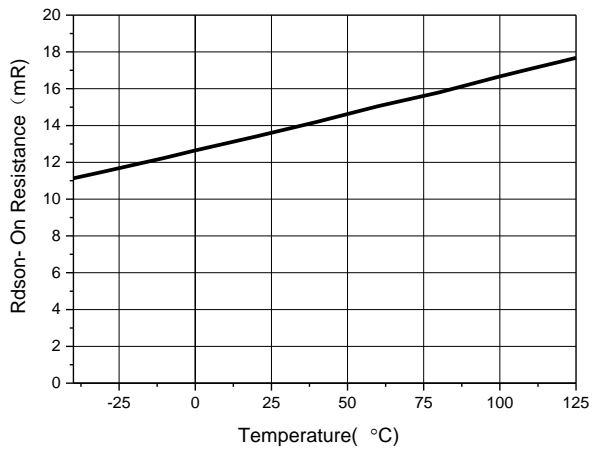


Fig8 RDS(ON) VS Temperature Of Junction

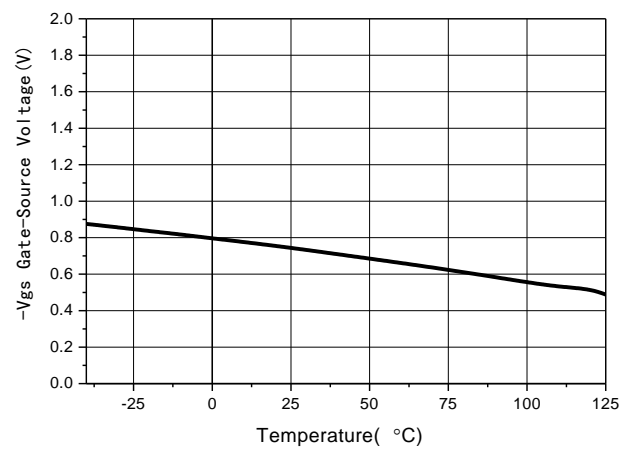
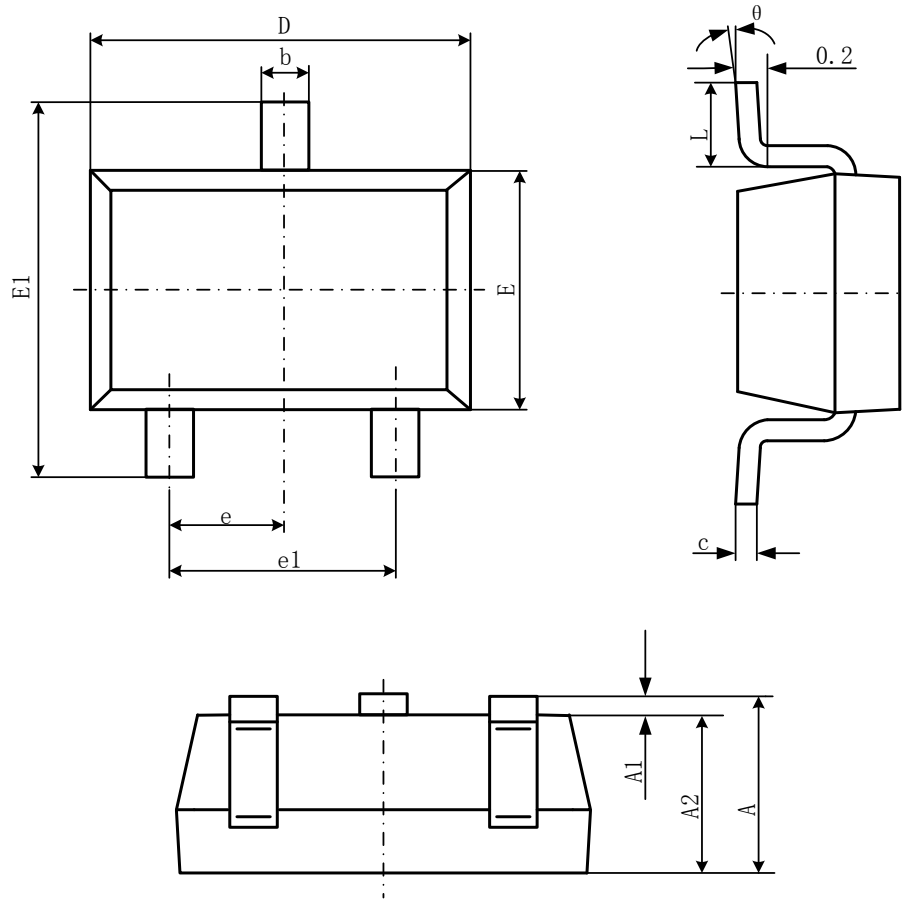


Fig8 VGS(TH) VS Temperature Of Junction

Package Information

- SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°